

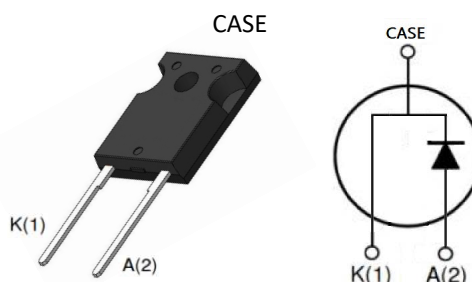
Features

- Ease of Paralleling
- Zero reverse recovery current
- Zero forward recovery voltage
- Temperature independent switching behaviour
- High temperature operation
- High frequency operation

Key Characteristics		
V_{RRM}	1200	V
$I_F, T_c \leq 140^\circ\text{C}$	10	A
Q_C	50	nC

Benefits

- Unipolar rectifier
- Substantially reduced switching losses
- No thermal run-away with parallel devices
- Reduced heat sink requirements



Applications

- Switch Mode Power Supplies (SMPS)
- Boost diodes in PFC or DC/DC stages
- Motor drives
- Solar application, UPS
- Power Switching Circuits

Part No.	Package Type	Marking
ASD10120C	TO-247-2	ASD10120C

Maximum Ratings

Parameter	Symbol	Test Condition	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}		1200	V
Surge Peak Reverse Voltage	V_{RSM}		1200	V
DC Blocking Voltage	V_{DC}		1200	V
Continuous Forward Current	I_F	$T_C=25^{\circ}C$	29	A
		$T_C=125^{\circ}C$	14	
		$T_C=140^{\circ}C$	10	
Repetitive Peak Forward Surge Current	I_{FRM}	$T_C=25^{\circ}C$, $t_p=10ms$, Half Sine Wave, $D=0.3$	50	A
Non-repetitive Peak Forward Surge Current	I_{FSM}	$T_C=25^{\circ}C$, $t_p=10ms$, Half Sine Wave	70	A
Power Dissipation	P_{TOT}	$T_C=25^{\circ}C$	139	W
		$T_C=110^{\circ}C$	60	W
Operating Junction	T_J		-55 $^{\circ}C$ to 175 $^{\circ}C$	$^{\circ}C$
Storage Temperature	T_{stg}		-55 $^{\circ}C$ to 175 $^{\circ}C$	$^{\circ}C$
Mounting Torque		M3 Screw	1	Nm
		6-32 Screw	8.8	lbf-in

Thermal Characteristics

Parameter	Symbol	Test Condition	Value	Unit
			Typ.	
Thermal resistance from junction to case	R_{thJC}		0.96	$^{\circ}C/W$

Electrical Characteristics

Parameter	Symbol	Test Conditions	Numerical		Unit
			Typ.	Max.	
Forward Voltage	V_F	$I_F=10A, T_j=25^{\circ}C$	1.5	1.7	V
		$I_F=10A, T_j=175^{\circ}C$	2.2	3	
Reverse Current	I_R	$V_R=1200V, T_j=25^{\circ}C$	10	50	μA
		$V_R=1200V, T_j=175^{\circ}C$	50	300	
Total Capacitive Charge	Q_C	$V_R=800V, T_j=150^{\circ}C$ $Q_C = \int_0^{V_R} C(V)dV$	50	-	nC
Total Capacitance	C	$V_R=0V, T_j=25^{\circ}C, f=1MHZ$	610	690	pF
		$V_R=400V, T_j=25^{\circ}C, f=1MHZ$	46	50	
		$V_R=800V, T_j=25^{\circ}C, f=1MHZ$	40	43	

Performance Graphs

1) Forward IV characteristics as a function of Tj :

2) Reverse IV characteristics as a function of Tj :

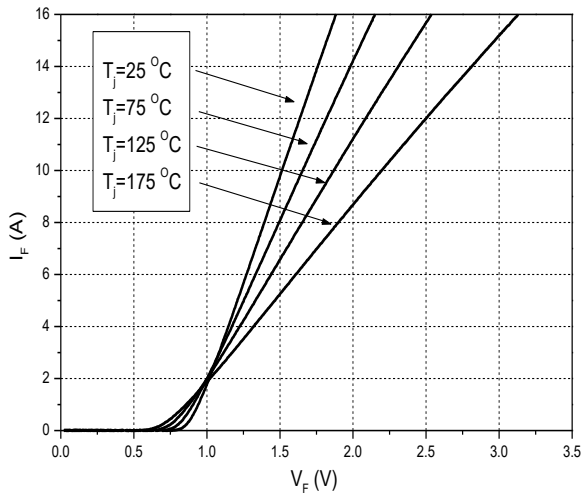


Figure 1. Forward Characteristics

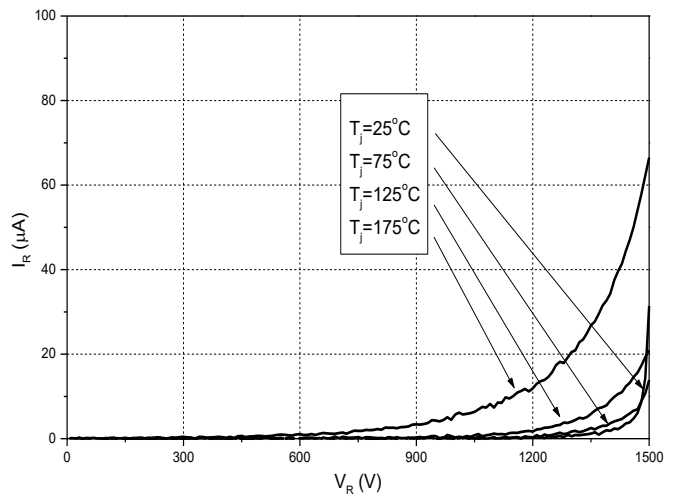


Figure2. Reverse Characteristics

3) Current Derating

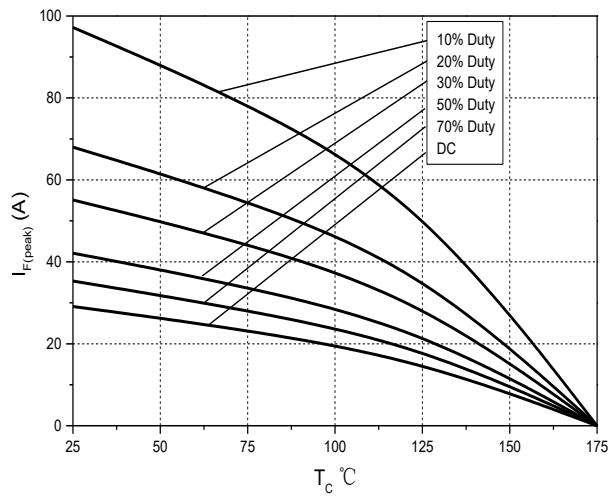


Figure 3.Current Derating

4) Capacitance vs. reverse voltage :

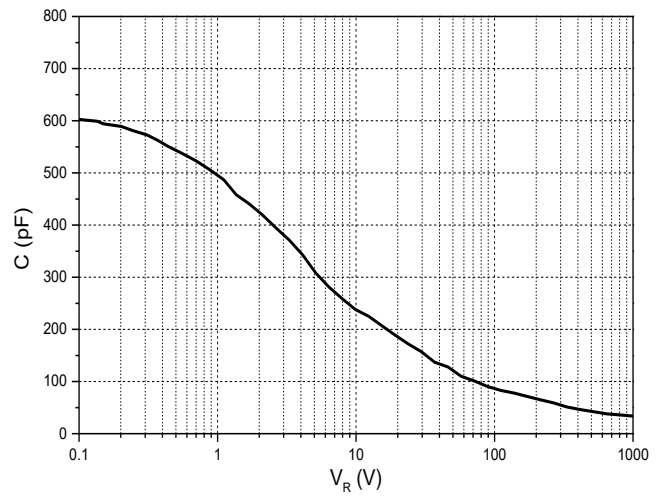
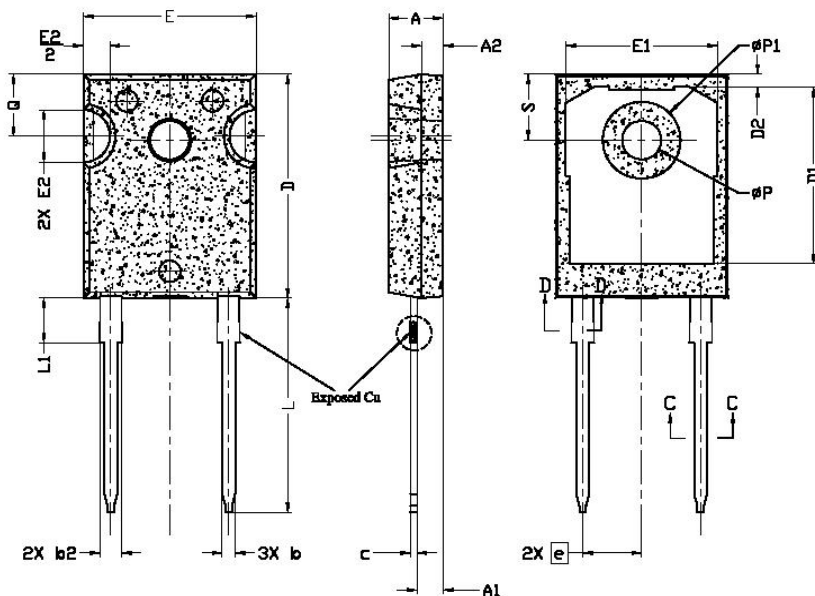


Figure 4.Capacitance vs. Reverse Voltage

Package TO-247-2



SYMBOL	DIMENSIONS			NOTES
	MIN.	NOM.	MAX.	
A	4,83	5,02	5,21	
A1	2,29	2,41	2,55	
A2	1,50	2,00	2,49	
b	1,12	1,20	1,33	
b1	1,12	1,20	1,28	
b2	1,91	2,00	2,39	6
b3	1,91	2,00	2,34	
c	0,55	0,60	0,69	6
c1	0,55	0,60	0,65	
D	20,80	20,95	21,10	4
D1	16,25	16,55	17,65	5
D2	0,51	1,19	1,35	
E	15,75	15,94	16,13	4
E1	13,46	14,02	14,16	5
E2	4,32	4,91	5,49	3
e	5,44BSC			
L	19,81	20,07	20,32	
L1	4,10	4,19	4,40	6
∅P	3,56	3,61	3,65	7
∅P1	7,19REF.			
Q	5,39	5,79	6,20	
S	6,04	6,17	6,30	

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